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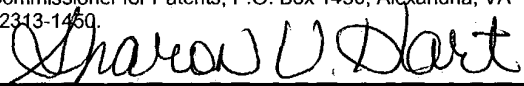
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For: METHOD OF REDUCING
CONTAMINATION-INDUCED
PROCESS VARIATIONS DURING
ION IMPLANTATION

SUBMISSION OF PRIORITY DOCUMENT

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Transmitted for filing herewith is the certified copy of the priority document – German
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Respectfully submitted,

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Prioritätsbescheinigung über die Einreichung einer Patentanmeldung

Aktenzeichen: 103 03 683.0

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Anmelder/Inhaber: ADVANCED MICRO DEVICES INC.,
Sunnyvale, Calif./US

Bezeichnung: A method of reducing contamination induced process
variations during ion implantation

IPC: C 23 C, H 01 L

Die angehefteten Stücke sind eine richtige und genaue Wiedergabe der ursprünglichen Unterlagen dieser Patentanmeldung.

München, den 20. Mai 2003
Deutsches Patent- und Markenamt
Der Präsident
Im Auftrag

A handwritten signature in black ink, appearing to be 'Wallner', written over the text 'Im Auftrag'.

Wallner

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**A METHOD OF REDUCING CONTAMINATION INDUCED PROCESS
VARIATIONS DURING ION IMPLANTATION**

A METHOD OF REDUCING CONTAMINATION INDUCED PROCESS VARIATIONS DURING ION IMPLANTATION

FIELD OF THE PRESENT INVENTION

The present invention generally relates to the fabrication of microstructures, such as integrated circuits, and more particularly to the incorporation of material species, such as dopants, into a substrate by ion implantation.

DESCRIPTION OF THE PRIOR ART

In many technical fields, implantation of ions into a substrate is a widely used technique to alter the characteristics of the substrate or of a specified portion thereof by incorporating a specified species. For example, the rapid development in the semiconductor industry is among others based on the capability of advanced implantation techniques to generate highly complex dopant profiles within tiny regions of semiconductive and dielectric materials. In implanting specified ions into a substrate not only a lateral implant profile may readily be obtained by providing correspondingly adapted implantation masks, for example formed as resist masks by photolithography, but also allows a vertical profile. To this end, an acceleration energy of the ions to be implanted is adjusted so as to deposit the majority of the ions at a specified depth of the substrate. Thus, contrary to doping a substrate by diffusion, laterally and in depth varying profiles may be created, thereby enabling the formation of complex dopant profiles as required, for instance in well and drain and source structures of advanced transistor elements. Moreover, by appropriately selecting the dose, i.e. the number of ions per unit area of the ion beam impinging on a substrate, comparably high concentrations of atoms with short time intervals may be incorporated into a substrate compared to other techniques, such as diffusion, and therefore renders ion implantation a cost-effective technique.

Although ion implantation offers a plurality of advantages over other techniques, there are several drawbacks involved in employing ion implantation. For instance, the highly energetic ions generate severe damage in crystalline structures that commonly has to be cured by annealing the substrate, thereby changing the dopant

profile as deposited owing to the unavoidable diffusion process during the anneal process. Similarly, the highly energetic ions may not completely be confined so as to exclusively hit the target, but may also interact with surface portions of the implantation tool, such as process chamber walls, inner surfaces of beam line, support means for fixing the substrate, and the like. During this interaction, metal atoms may be liberated and may become ionized and conveyed to the substrate where the metal atoms may be incorporated into the substrate.

A further source of contamination is the cross contamination of the implantation tool and thus of a substrate processed therein. Cross contamination may readily occur when an implantation tool is operated with a first dopant species, which may according to the implantation kinetics also interact with some surface portion of the tool that are exposed to the ions of the first species. Accordingly, ions of the first species may be incorporated into those exposed portions. Thereafter, the implantation tool may be used to implant a second, different species into the same or a different type of substrate, wherein then the atoms of the first species may be released by getting sputtered off the exposed surface portions. These atoms may be ionized and may then be deposited on and in the substrate along with the ions of the second species. In modern integrated circuits, however, even minute amounts of dopant variations may lead to significant variations of device characteristics due to the extremely complex dopant profiles required to adjust the properties of transistors having minimum feature sizes of $0.1\mu\text{m}$ and even less.

Especially in sophisticated CMOS techniques the well and the so-called halo implants require sufficiently steep dopant profiles to obtain the desired transistor performance. That is, usually heavy dopant species, such as arsenic, indium or antimony are used at high dosage in the range of approximately 10^{12} to 10^{14} ions per cm^2 so as to confine the dopants within the region of interest with a desired small tolerance as typically heavy ions tend to get less scattered and thus less spread during the implantation process. Moreover, subsequent anneal processes less affect the profile as deposited as is the case for lighter atoms. However, the heavy ions provided at a high dose may lead to an increased cross contamination, especially when the implantation tool is used for the implantation of light ions such as boron and phosphorus at low energy as is required for source and drain implants

and the like. Exclusively employing a specified tool with a certain dopant species may, however, not be considered an attractive option owing to cost concerns.

Therefore, a need exists for an effective technique that allows to reduce cross contamination during ion implantation when changing the dopant species.

SUMMARY OF THE INVENTION

The present invention is generally directed at an improved clean sequence prior to or during the implantation of a species, wherein especially the cleansing effect with respect to heavy ions, such as indium and antimony is improved. This is accomplished by operating an implantation tool with xenon, for example, after the implantation species on the implantation process has been changed.

According to one illustrative embodiment of the present invention a method comprises operating an implantation tool with a first species including a first dopant and operating the implantation tool with xenon as an implant precursor to reduce residues of the first species from the implantation tool. Moreover, the implantation tool is then operated with a second species including a second dopant.

In a further illustrative embodiment of the present invention a method of doping a substrate comprises operating an implantation tool with xenon as the implantation species prior to installing the substrate in the implantation tool to reduce contaminating particles. Then, the implantation tool is operated with the substrate mounted therein to implant a first species of dopants in the substrate.

According to still another illustrative embodiment of the present invention a method of doping substrates comprises mounting a substrate in an implantation tool and operating the implantation tool with a first species of dopants to implant the first dopant into a crystalline region of the substrate. The implantation tool is then operated with xenon as the implantation species to substantially amorphize a portion of the crystalline region. Finally, the implantation tool is operated with a second species of dopants to implant the second dopants into the substantially amorphized portion.

BRIEF DESCRIPTION OF THE DRAWINGS

Further advantages, objects and embodiments of the present invention are defined in the appended claims and will become more apparent with the following detailed description when taken with reference to the accompanying drawing, in which:

Fig. 1 schematically depicts in a very simplified manner an implantation tool which may be used in accordance with the present invention.

DETAILED DESCRIPTION

While the present invention is described with reference to the embodiments as illustrated in the following detailed description as well as in the drawing, it should be understood that the following detailed description as well as the drawing are not intended to limit the present invention to the particular illustrative embodiments disclosed, but rather the described illustrative embodiments merely exemplify the various aspects of the present invention, the scope of which is defined by the appended claims.

As previously pointed out, cross contamination is a potential risk when an implantation tool is to be used for different implantation species, as is commonly the case in the field of research and industrial production due to high cost and significant floor space required for plural implantation tools. Moreover, the plurality of dopants used in sophisticated devices does practically prevent manufactures from using implantation tools dedicated to only one dopant species. Therefore, cleaning steps with argon as an implant species are frequently performed after one species is replaced by another species prior to actually implanting the new species. An argon clean step usually takes approximately 15 to 30 minutes, wherein it turns however, that argon exhibits a reduced cleaning effect for indium and antimony, entailing extremely long clean cycles that significantly increase process times. According to the inventors' findings xenon may be used during the change of species, wherein a significantly improved clean effect may be achieved even with

reduced cleaning intervals compared to argon clean cycles. Moreover, the cleaning process with xenon itself may advantageously be used for processing a substrate to amorphize crystalline portions by the inert xenon ions.

With reference to Fig. 1 further illustrative embodiments will now be described.

In Fig. 1 an illustrative example of an implantation tool 100 comprises a process chamber 101 including a substrate holder 102 with a substrate 104 placed thereon and fixed with support members 103. The process chamber 101 may be connected to a vacuum pump 107 and a source of purge gas 108 to establish a desired atmosphere during the implantation process and to allow purging the process chamber 101 according to process requirements. A beam line 106 is connected to the process chamber 101 and separated therefrom by a shutter 105. At the other end the beam line 106 is connected to ionization means 109, including means (not shown) for ionizing a precursor gas supplied thereto. Moreover, any means for creating and shaping an ion beam are not shown for the sake of clarity. Connected to the ionization means are a first source of dopant species 110 and a second source of dopant species 111. For example, the first source 110 may comprise a species for generating indium, arsenic or antimony dopants, as are often employed in forming well and halo implants in advanced field effect transistors of modern CMOS circuits. The second source may comprise a species for generating light dopants such as boron and phosphorus, commonly used for source/drain regions, threshold implants, channel stop implants, anti-punchthrough implants, and the like.

Moreover, a xenon source 112 is connected to the ionization means 109, wherein in one embodiment, the xenon source may be provided as a mobile bottle that may additionally be switchably connected to a further clean gas source (not shown) such as an argon source. This allows to alternatively use argon and xenon while requiring only a single connection to the implantation tool 100 so that the present invention may readily be practiced with existing tools without elaborate modifications of the tool. In one embodiment, the xenon source 112 is used with implantation tool EHP500i, available from Varian, wherein the xenon source 112 may be connected to an argon line by a switchable valve (not shown) so that each of the slots for dopant precursors, may still be used for commonly required species,

such as the sources 110 and 111 and the argon for conventional processes and xenon may selectively be used.

In operation, for example the first source 110, including for example a precursor for heavy dopants, such as indium, may be connected to the ionization means 109 to start implantation of a first species into the substrate 104. A dose may be selected in accordance with process specifications and may for typical well and halo implants be in the range of approximately 10^{12} to 10^{14} ions per cm^2 . It should be appreciated that the above values are illustrative only and any other dosage may be used if appropriate. The implantation energy depends on the implantation depth and the species and may typically range for the above mentioned well and halo implants from approximately 30 keV to 150 keV.

After processing one or more of substrates, such as the substrate 104, it may be necessary to operate the implantation tool 100 with the species provided by source 111. To this end, in one embodiment the xenon source 112 may be connected to the ionization means 109 after removal of the substrate 104, and the implantation tool may be operated with xenon at a dose of approximately 10^{14} to 10^{15} ions per cm^2 . The acceleration energy may be adjusted to approximately 30keV to 200keV, and, in one embodiment, to approximately 40keV to 160keV. A duration of the cleaning interval may range from approximately 2 to 15 minutes or even longer if desired. During operation of the implantation tool 100 with xenon residues of the preceding dopants, especially of indium and antimony, are effectively removed. It has been found that the cleaning effect of xenon may be up to ten times as efficient than with an argon process. In one embodiment, the implantation tool 100 may be operated during the xenon clean step with a dummy substrate (not shown) placed on the substrate holder 102. The dummy substrate may be comprised of any appropriate material that does not substantially lead to a further cross contamination with a subsequent implant cycle. For instance, a bare silicon wafer may be used as dummy substrate, since any silicon residues sputtered off the dummy wafer may not negatively affect a subsequent implant cycle due to its substantially inert behavior in other silicon based product substrates.

In one illustrative embodiment, the substrate 104 may represent a product substrate that is to be treated so as to substantially amorphize a predefined portion of a crystalline semiconductor region. As previously noted, modern CMOS transistor structures may require a complex dopant profile including halo profiles within their well regions and in the drain/source regions, which typically include so-called extension regions having a shallow p-n junction formed with the surrounding channel region. It has been found that the constraints for the generation including the required anneal processes of these dopant profiles may somewhat be relaxed when the crystalline structure of the corresponding region is substantially amorphized prior the formation of the halo and source/drain implants. Since the electronic characteristics of the amorphized region, except for the dopant atoms deliberately introduced into a portion of the amorphized region, should substantially not be altered after re-crystallization, typically inert ions are used for the amorphization implant. To obtain the desired destruction of the crystalline structure preferably heavy ions are used at a high dosage. Thus, the xenon clean may advantageously be used as an amorphization implantation or at least as a part of the amorphization implant, since the any cross contamination particles may not very efficiently affect the characteristics of the amorphized region due to high dosage and the deep penetration depth of the implantation.

In other embodiments, the implantation tool 100 may be operated without a any substrate. Irrespective whether the implantation tool 100 is operated with or without a substrate, the atmosphere within the process chamber 101 may be established such that a maximum cleaning effect is achieved. For instance, the pressure within the chamber 101 may be increased compared to regular operating conditions so as to obtain a higher degree of scattering of the xenon ions, thereby more effectively removing previously deposited dopants. To this end, the purge gas source 108 may be connected to the chamber 101 to provide a desired flow rate of purge gas, for example xenon or argon gas. Similarly, the pressure in the beam line 106, if not controlled by the pump 107, may also be newly adapted to a higher value during the cleaning step. The pressure in the chamber 101 and/or the beam line 109 may be adjusted to approximately 10 to 100 mTorr.

In other embodiments, the chamber 101 may one or more times be purged by connecting the purge gas source 108 to the chamber 101 while discontinuing the clean implantation process. In this way, the clean efficiency may be enhanced without unduly prolonging the overall process time of the clean process as a required vacuum pressure for resuming of the implant, either as clean process or as regular process, may be obtained within approximately 1 or 2 minutes with a typical vacuum pump.

It should be noted that although the present invention is especially advantageous when used as clean or amorphization process when replacing a heavy dopant species by a light species intended to be implanted by relatively low energies, the present invention may also be applied for any clean process irrespective of the dopant species previously used in the implantation tool.

Thus, the present invention provides for an efficient clean sequence by using xenon instead of, for example, argon, wherein due to enhanced cleaning capability an overall reduction of process time is achieved by increasing implant tool utilization.

Further modifications and variations of the present invention will be apparent to those skilled in the art in view of this description. Accordingly, the description is to be construed as illustrative only and is for the purpose of teaching those skilled in the art the general manner of carrying out the present invention. It is to be understood that the forms of the invention shown and described herein are to be taken as the presently preferred embodiments.

CLAIMS

1. A method comprising:

operating an implantation tool with a first species including a first dopant;

operating said implantation tool with xenon as an implant precursor to reduce residues of the first species from said implantation tool; and

operating said implantation tool with a second species including a second dopant.

2. The method of claim 1, wherein said first dopant comprises at least one of arsenic, indium and antimony.

3. The method of claim 2, wherein said second dopant comprises one of boron and phosphorus.

4. The method of claim 1, wherein said xenon is accelerated with an energy in the range of approximately 30 to 200 keV.

5. The method of claim 1, wherein said xenon is accelerated with an energy in the range of approximately 40 to 160 keV.

6. The method of claim 1, wherein a dose is in the range of approximately $1 \cdot 10^{13}$ to $1 \cdot 10^{14}$ ions per cm^2 , when operating said implantation tool with xenon.

7. The method of claim 1, wherein said implantation tool is operated with xenon for a time interval in the range of approximately 2 to 10 minutes.

8. The method of claim 1, further comprising purging and evacuating said implantation tool at least once prior to operating said implantation tool with said second species.

9. The method of claim 1, wherein operating said implantation tool with said first species includes implanting said first dopant into a semiconductor region of a substrate to form one of a well profile and a halo profile for a transistor structure.

10. The method of claim 9, wherein operating said implantation tool with said xenon includes implanting xenon ions into said semiconductor region to amorphize a portion thereof.

11. The method of claim 1, wherein operating said implantation tool with said xenon is performed without a substrate placed in said implantation tool.

12. The method of claim 1, wherein operating said implantation tool with said xenon is performed with a substrate that has not been exposed to said first species.

13. A method of doping a substrate, the method comprising:

operating an implantation tool with xenon as the implantation species prior to installing said substrate in the implantation tool to reduce contaminating particles; and

operating said implantation tool with the substrate mounted therein to implant a first species of dopants in the substrate.

14. The method of claim 13, further comprising operating said implantation tool with a second species other than said first species prior to operating said implantation tool with xenon.

15. The method of claim 13, wherein said first species is one of arsenic, indium, antimony, boron and phosphorus.

16. The method of claim 14, wherein said second species is one of arsenic, indium, antimony, boron and phosphorus.

17. The method of claim 14, wherein said first species is one of boron and phosphorus.

18. The method of claim 14, wherein said second species is one of arsenic, indium and antimony.

19. The method of claim 13, wherein said xenon is accelerated with an energy in the range of approximately 30 to 200 keV.

20. The method of claim 13, wherein said xenon is accelerated with an energy in the range of approximately 40 to 160 keV.

21. The method of claim 13, wherein a dose is in the range of approximately $1 \cdot 10^{13}$ to $1 \cdot 10^{14}$ ions per cm^2 , when operating said implantation tool with xenon.

22. The method of claim 13, wherein said implantation tool is operated with xenon for a time interval in the range of approximately 2 to 10 minutes.

23. A method of doping substrates, the method comprising:

mounting a substrate in an implantation tool;

operating said implantation tool with a first species of dopants to implant said first dopant into a crystalline region of said substrate;

operating said implantation tool with xenon as the implantation species to substantially amorphize a portion of said crystalline region; and

operating said implantation tool with a second species of dopants to implant said second dopants into said substantially amorphized portion.

24. The method of claim 23, wherein said xenon is implanted with an energy in the range of approximately 30 to 200 keV.

25. The method of claim 23, wherein said xenon is implanted with an energy in the range of approximately 40 to 160 keV.

26. The method of claim 23, wherein a dose is in the range of approximately $1 \cdot 10^{13}$ to $1 \cdot 10^{14}$ ions per cm^2 , when operating said implantation tool with xenon.

27. The method of claim 23, further comprising, prior to amorphizing said portion, operating said implantation tool with xenon when said substrate is removed from said implantation tool to reduce residues of said first species.

ABSTRACT

When changing a dopant species in an implantation tool, typically a clean process is performed to reduce cross contamination, which is considered a major issue in implant cycles applied in advanced CMOS processes. Especially the employment of an implanter previously used for heavy ions may generate increased cross contamination when subsequently used for boron or phosphorus implants at moderate energies. A clean implant process using xenon gas may effectively reduce this cross contamination at shorter process times compared to a conventional argon clean step.

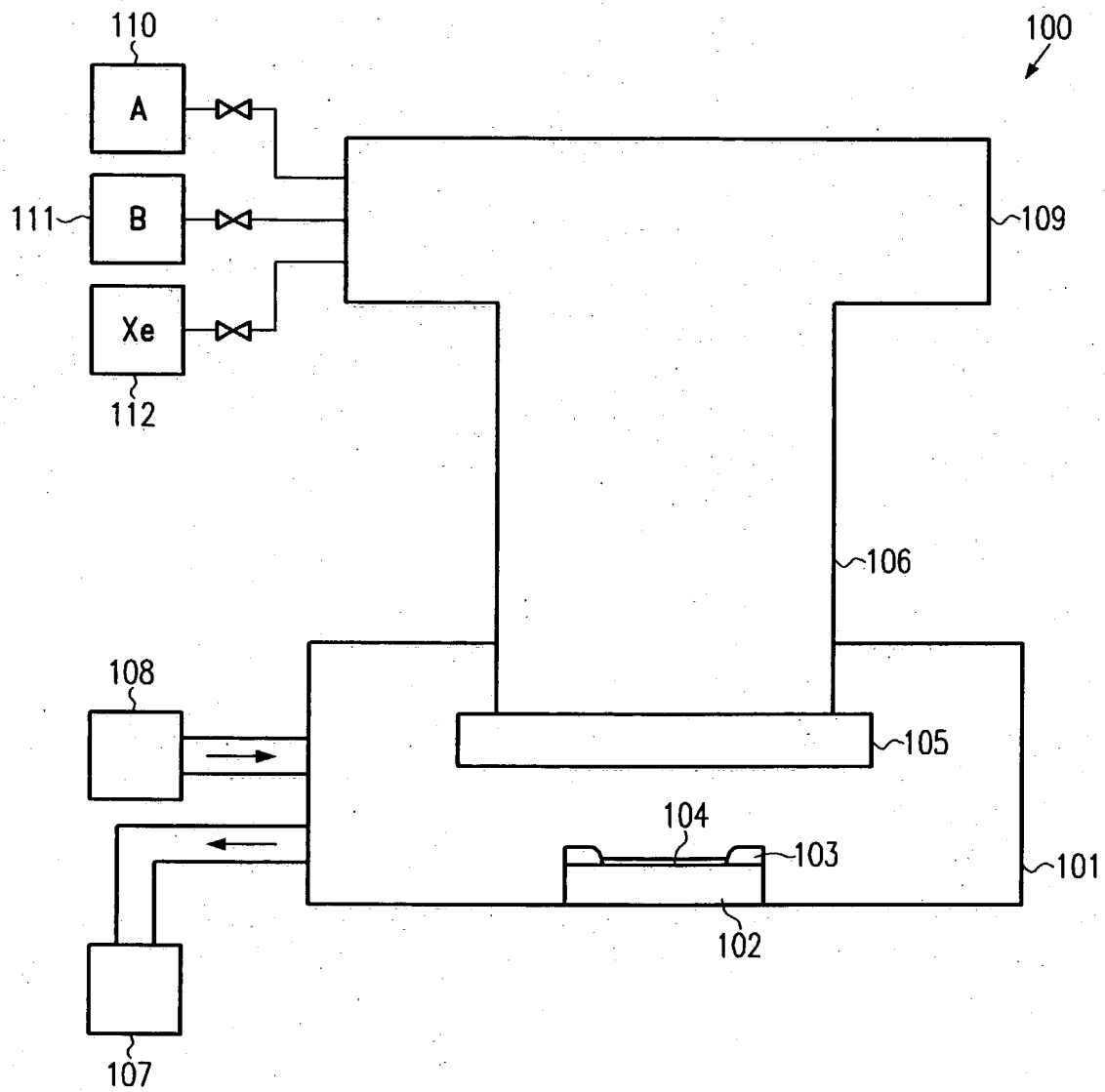


Fig.1